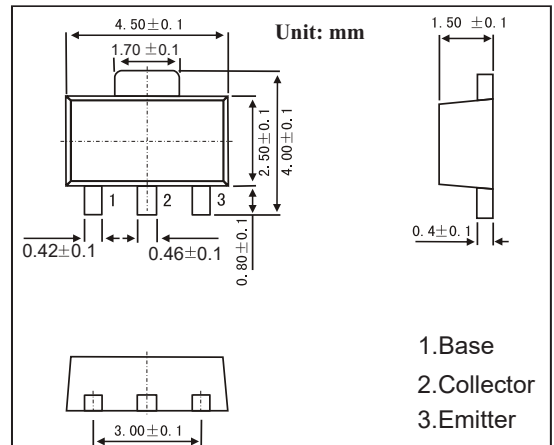


SOT-89 Plastic-Encapsulate Transistors
FEATURES

- Small Flat Package
- High Speed Switching Time
- Low Collector-emitter saturation voltage
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:SOT-23molded plasti
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2	A
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=0.5A$	82		390	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=2A$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1A, I_B=50mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1A, I_B=50mA$			1.2	V
Transition frequency	f_T	$V_{CE}=2V, I_C=0.5A, f=100MHz$		120		MHz

RATINGS AND CHARACTERISTIC CURVES

